AMENDMENTS TO THE CLAIMS

Listing Of Claims

Claims 1-152 (Canceled)

153. (withdrawn) A semiconductor component comprising:

a thinned semiconductor die having a circuit side, a thinned back side and a plurality of peripheral edges;

a first polymer layer covering the circuit side and the edges; and

a second polymer layer covering the back side.

154. (withdrawn) The semiconductor component of claim 153 further comprising a plurality of die contacts on the die, and a plurality of contact bumps on the die contacts embedded in the first polymer layer.

155. (withdrawn) The semiconductor component of claim 154 further comprising a plurality of terminal contacts on the contact bumps.

156. (withdrawn) The semiconductor component of claim 154 wherein the terminal contacts comprise bumps or balls in a grid array, or planar pads configured as an edge connector.

157. (withdrawn) The semiconductor component of claim 154 wherein the second polymer layer is opaque to radiation at a selected wavelength.

158. (withdrawn) The semiconductor component of claim 154 wherein the second polymer layer comprises a wafer level underfill tape.

159. (withdrawn) The semiconductor component of claim 154 wherein the second polymer layer comprises parylene.

160. (withdrawn) The semiconductor component of claim 154 wherein the second polymer layer comprises a photoresist.

161. (withdrawn) The semiconductor component of claim 154 wherein the second polymer layer comprises a tape.

162. (withdrawn) The semiconductor component of claim 154 wherein the second polymer layer comprises a stereographic imageable resist.

163. (withdrawn) The semiconductor component of claim 154 wherein a thickness of the component is about 28.5 mils.

164. (withdrawn) The semiconductor component of claim 154 wherein a thickness of the die is about 10 μm to 720 μm.

165. (withdrawn) The semiconductor component of claim 154 further comprising a polymer tape attached to the thinned back side which is opaque to radiation at a selected wavelength, and a laser marking on the polymer tape.

166. (withdrawn) The semiconductor component of claim 154 further comprising a conductive via in the thinned substrate.

167. (withdrawn) The semiconductor component of claim 166 wherein the conductive via comprises a conductive

member exposed with respect to the substrate to provide a pin terminal contact.

168. (withdrawn) The semiconductor component of claim 166 wherein the conductive via comprises a conductive member, and the component further comprises a terminal contact on the back side in electrical communication with the conductive via.

169. (withdrawn) The semiconductor component of claim 166 wherein the conductive via comprises a reverse bias junction.

170. (currently amended) A chip scale semiconductor component comprising:

a thinned semiconductor die having an outline, a circuit side, a back side, four peripheral edges, and a plurality of die contacts on the circuit side;

a plurality of contact bumps on the die contacts;

a first polymer layer covering the circuit side, the contact bumps and the peripheral edges, the first polymer layer having a selected thickness on each peripheral edge;

a second polymer layer covering the back side, the first polymer layer and the second polymer layer encapsulating the die on six sides such that the component has an outline equal to that of the die plus the selected thickness of the first polymer layer on each peripheral edge; and

a plurality of terminal contacts on the contact bumps.

171. (currently amended) The semiconductor component of claim 170 wherein the selected thickness is about 1 mil. ~~contact bumps and the first polymer layer are planarized to a same surface.~~

172. (previously presented) The semiconductor component of claim 170 wherein the contact bumps comprise metal bumps.

173. (previously presented) The semiconductor component of claim 170 wherein the terminal contacts comprise conductive bumps or balls.

174. (currently amended) The semiconductor component of claim 170 wherein the first polymer layer has a ~~planarized~~ first planar surface.

175. (currently amended) The semiconductor component of claim 170 wherein the second polymer layer has a ~~planarized~~ second planar surface.

176. (currently amended) The semiconductor component of claim 170 further comprising a plurality of conductive vias in the thinned die in electrical communication with the die contacts and with the terminal contacts.

177. (previously presented) The semiconductor component of claim 176 further comprising a plurality of second die contacts on the second polymer layer in electrical communication with the conductive vias.

178. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a photopolymer.

179. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a wafer level underfill.

180. (withdrawn) A semiconductor component comprising:

a thinned semiconductor die having a circuit side, a back side and four peripheral edges;

a circuit side polymer layer covering the circuit side;

a plurality of edge polymer layers covering the four peripheral edges, the edge polymer layers and the circuit side polymer layer comprising a continuous layer of material, the edge polymer layers comprising portions of polymer filled trenches; and

a back side polymer layer covering the back side.

181. (withdrawn) The semiconductor component of claim 180 further comprising a plurality of die contacts on the die, and a plurality of contact bumps on the die contacts embedded in the circuit side polymer layer.

182. (withdrawn) The semiconductor component of claim 180 further comprising a plurality of die contacts on the die, and a plurality of planarized contact bumps on the die contacts embedded in the circuit side polymer layer and planarized to a surface thereof.

183. (withdrawn) The semiconductor component of claim 182 further comprising a plurality of terminal contacts on the contact bumps.

184. (withdrawn) The semiconductor component of claim 180 further comprising a plurality of conductive vias through the die

185. (withdrawn) The semiconductor component of claim 180 further comprising a plurality of conductive vias through the die including exposed portions configured as pins.

186. (withdrawn) The semiconductor component of claim 180 further comprising a plurality of conductive vias through the die including tip portions, a plurality of conductors on the back side in electrical communication with the conductors, and a plurality of terminal contacts on the back side in electrical communication with the tip portions.

187. (withdrawn) The semiconductor component of claim 180 wherein the back side polymer layer is opaque to radiation at a selected wave length.

188. (withdrawn) The semiconductor component of claim 180 wherein the back side polymer layer comprises a wafer level underfill.

189-261 (canceled)